

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
RMS on-state current @ $T_c = 80^\circ\text{C}$	$I_{T(RMS)}$	16	A
Mean on-state current @ $T_c = 80^\circ\text{C}$	$I_{T(AV)}$	10	A
Non-repetitive surge peak on-state current @ $T_j \leq 125^\circ\text{C}$ $t = 8.3\text{ms}$ $t = 10\text{ms}$	I_{TSM}	157 150	A
I^2t for fusing @ $T_j \leq 125^\circ\text{C}$, $t = 10\text{ms}$	I^2t	112.5	A^2s
Critical rate of rise of on-state current	di/dt	100	$\text{A}/\mu\text{s}$
Operating junction temperature range; non-"A" Operating junction temperature range; "A"	T_j	-40 to +100 -65 to +125	$^\circ\text{C}$
Storage temperature range; non-"A" Storage temperature range; "A"	T_{stg}	-40 to +125 -65 to +125	$^\circ\text{C}$

VOLTAGE RATINGS

$T_j = 125^\circ\text{C}$	2N1842(A)	2N1843(A)	2N1844(A)	2N1845(A)	2N1846(A)	2N1847(A)	2N1848(A)	2N1849(A)	2N1850(A)
$V_{DRM} = V_{RRM}$	25	50	100	150	200	250	300	400	500

VOLTAGE RATINGS

$T_j = 125^\circ\text{C}$	TR6010	TR7010	TR8010	TR9010	TR1010	TR1110	TR1210
$V_{DRM} = V_{RRM}$	600	700	800	900	1000	1100	1200

THERMAL RESISTANCE

Thermal resistance	Symbol	Value	Unit
Junction to case for DC	$R_{th(j-c)}$	2	$^\circ\text{C}/\text{W}$
Case to heatsink	$R_{th(c-h)}$	0.4	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Value			Unit	Test conditions			
		Min	Typ	Max					
Gate trigger current	I_{GT}	-	-	80	mA	$T_j = 25^\circ\text{C}$	$V_D = 12\text{V}$	$R_L = 33\Omega$	$t_p \geq 20\mu\text{s}$
Gate trigger voltage	V_{GT}	-	-	3	V	$T_j = 25^\circ\text{C}$	$V_D = 12\text{V}$	$R_L = 33\Omega$	$t_p \geq 20\mu\text{s}$
Peak gate voltage	V_{GD}	0.25	-	-		$T_j = 125^\circ\text{C}$	$V_D = V_{DRM}$	$R_L = 3.3\Omega$	
Holding current	I_H	-	20	-	mA	$T_j = 25^\circ\text{C}$	$I_T = 0.5\text{A}$	Gate open	
Peak on-state voltage	V_{TM}	-	-	2.2	V	$T_j = 25^\circ\text{C}$	$I_{TM} = 30\text{A}$	$t_p = 10\text{ms}$	
Maximum off-state current	I_{DRM}	-	-	5	mA	$T_j = 125^\circ\text{C}$	V_{DRM} specified		
Maximum off-state current	I_{RRM}	-	-	5	mA	$T_j = 125^\circ\text{C}$	V_{RRM} specified		
Turn on time	t_{gt}	-	2	-	μs	$T_j = 25^\circ\text{C}$ $I_G = 200\text{mA}$	$I_T = 30\text{A}$ $di_G/dt = 2\text{A}/\mu\text{s}$	$V_D = V_{DRM}$	

2N1842-2N1850A TR1010-TR9010

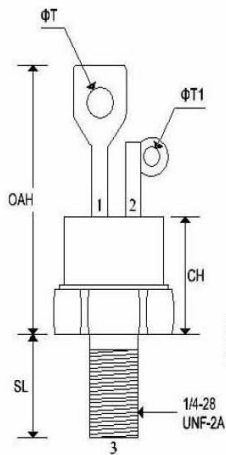
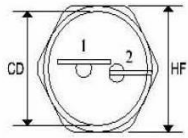
SILICON CONTROLLED RECTIFIER

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Value			Unit	Test conditions			
		Min	Typ	Max					
Turn off time	t_q	-	100	-	μs	$T_J = 125^\circ\text{C}$ $di_R/dt = 30\text{A}/\mu\text{s}$	$I_T = 10\text{A}$ $dv/dt = 20\text{V}/\mu\text{s}$	$V_R = 30\text{V}$	$V_D = 0.67 V_{\text{DRM}}$ Gate open
Critical rise of off-state voltage	dv/dt	100	-	-	$\text{V}/\mu\text{s}$	$T_J = 125^\circ\text{C}$	Linear slope up to $0.67 V_{\text{DRM}}$ specified		

MECHANICAL CHARACTERISTICS

Case	TO-48
Marking	Alpha-numeric
Polarity	Cathode



	TO-48			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	-	0.543	-	13.793
CH	-	0.550	-	13.970
HF	0.544	0.563	13.817	14.301
OAH	-	1.193	-	30.303
SL	0.422	0.453	10.718	11.507
ΦT	0.125	0.165	3.175	4.191
ΦT_1	0.060	0.075	1.524	1.905

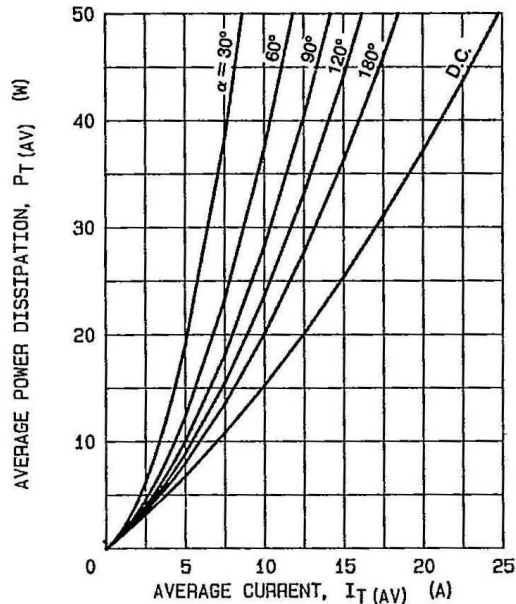


FIG.1 - MAXIMUM ON-STATE POWER DISSIPATION FOR SINUSOIDAL CURRENT WAVEFORM

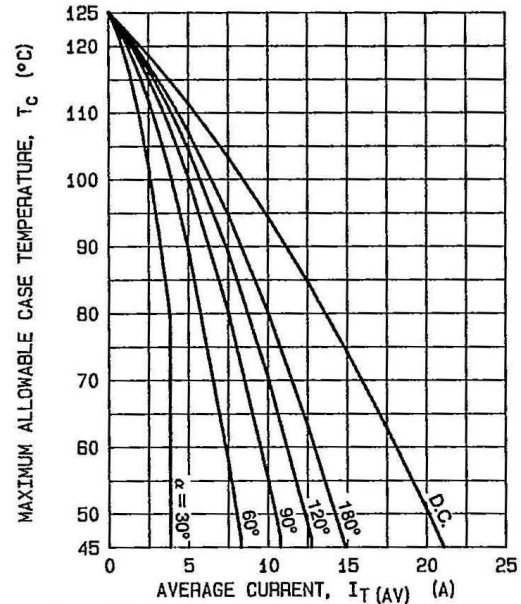


FIG.2 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR SINUSOIDAL CURRENT WAVEFORM

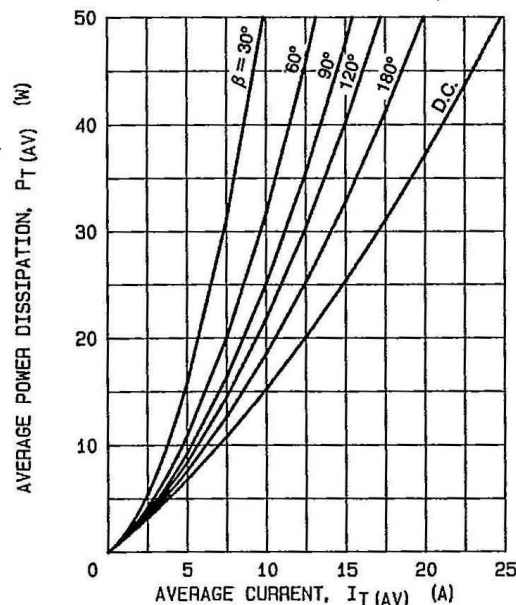
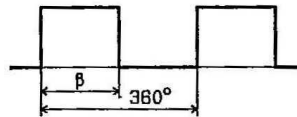


FIG.3 - MAXIMUM ON-STATE POWER DISSIPATION FOR RECTANGULAR CURRENT WAVEFORM

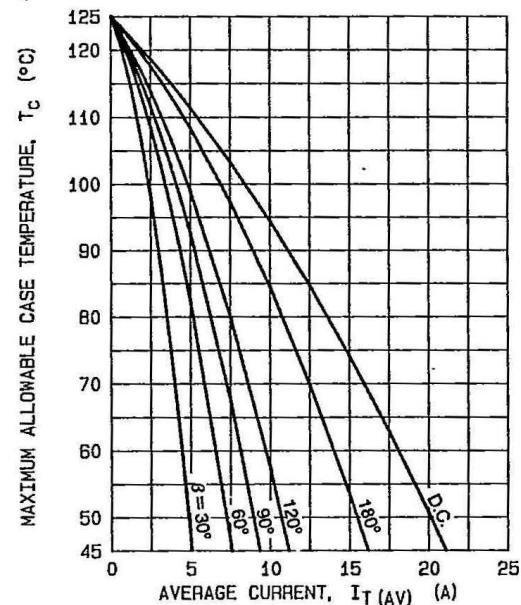


FIG.4 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR RECTANGULAR CURRENT WAVEFORM

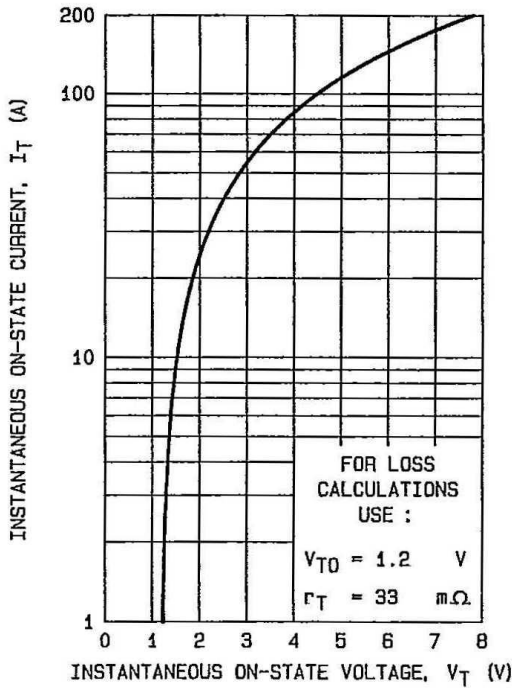


FIG.5 - MAXIMUM ON-STATE CONDUCTION CHARACTERISTIC ($T_J = 125^\circ\text{C}$).

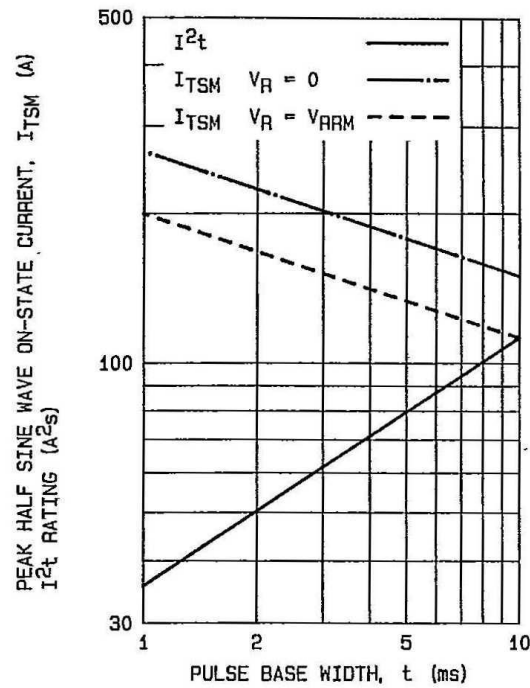


FIG.6 - NON REPETITIVE SUB-CYCLE SURGE ON-STATE CURRENT AND I^2t RATING (INITIAL $T_J = 125^\circ\text{C}$).

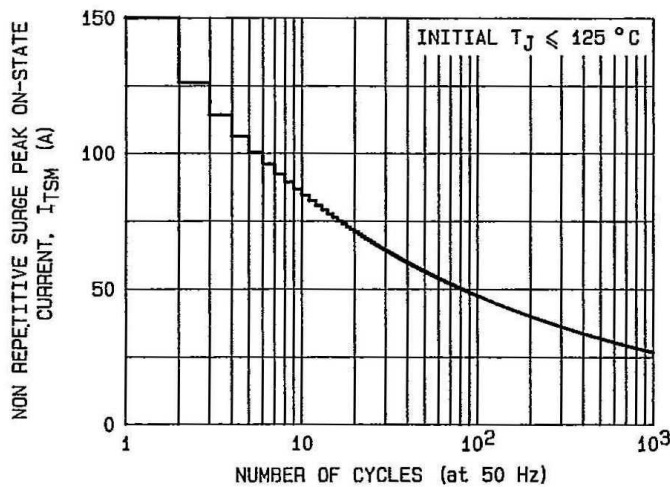


FIG.7 - NON REPETITIVE SURGE PEAK ON-STATE CURRENT VERSUS NUMBER OF CYCLES.

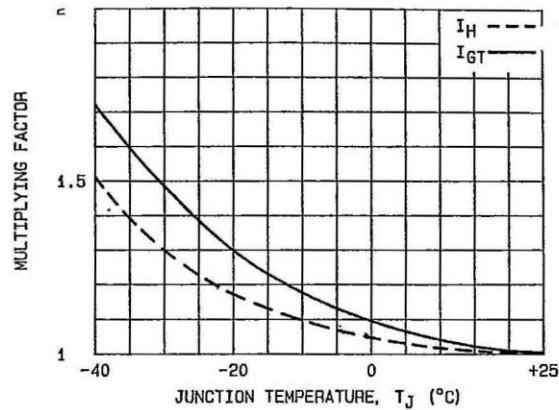


FIG.8 - RELATIVE VARIATION OF GATE TRIGGER CURRENT AND HOLDING CURRENT VERSUS JUNCTION TEMPERATURE.

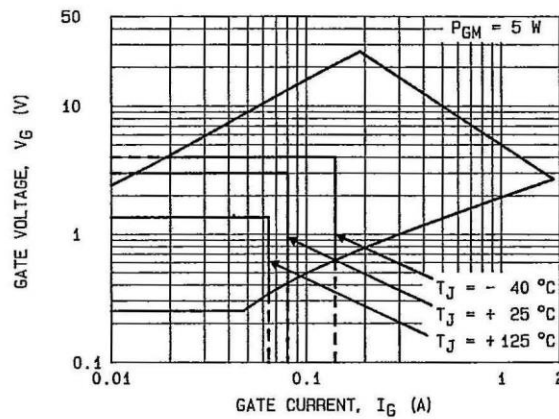


FIG.8 - GATE TRIGGER CHARACTERISTICS.

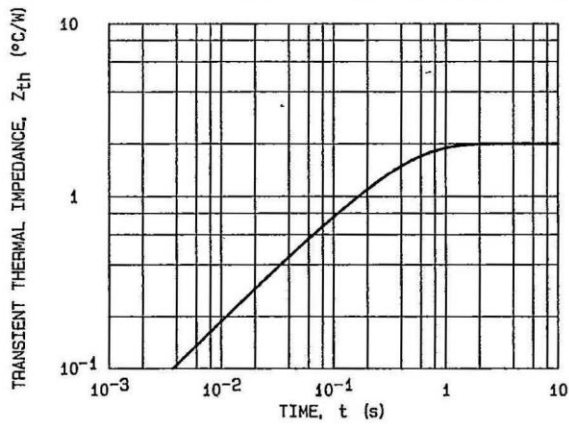


FIG.10 - TRANSIENT THERMAL IMPEDANCE JUNCTION TO CASE.

Conduction angle (α, β)	Effective thermal resistance ($^{\circ}\text{C}/\text{W}$) junction to case	
	Sinusoidal	Rectangular
180°	2.23	2.18
120°	2.31	3.09
90°	2.47	3.50
60°	2.88	3.91
30°	3.71	4.94